

# BT169H

Thyristor, logic level, high voltage

Rev. 01 — 31 March 2008

Product data sheet

## 1. Product profile

### 1.1 General description

Passivated sensitive gate thyristor in a SOT54 plastic package.

### 1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs
- High blocking voltage
- Direct interfacing to low power gate drive circuits

### 1.3 Applications

- General purpose switching and phase control
- Earth leakage circuit breakers or Ground Fault Circuit Interrupters (GFCI)

### 1.4 Quick reference data

- $V_{RRM}, V_{DRM} \leq 800$  V
- $I_{T(RMS)} \leq 0.8$  A
- $I_{T(AV)} \leq 0.5$  A
- $I_{GT} \leq 100$   $\mu$ A
- $I_{TSM} \leq 9$  A ( $t = 10$  ms)

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	anode (A)	 SOT54 (TO-92)	 A — — K G sym037
2	gate (G)		
3	cathode (K)		

### 3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BT169H	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

### 4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$V_{RRM}$	repetitive peak reverse voltage		-	800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$ ; see <a href="#">Figure 1</a>	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	all conduction angles; see <a href="#">Figure 4</a> and <a href="#">5</a>	-	0.8	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ °C}$ prior to surge; see <a href="#">Figure 2</a> and <a href="#">3</a>			
		$t = 10\text{ ms}$	-	9	A
		$t = 8.3\text{ ms}$	-	10	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$	-	0.41	$A^2s$
$di_T/dt$	rate of rise of on-state current	$I_{TM} = 2\text{ A}$ ; $I_G = 10\text{ mA}$ ; $di_G/dt = 100\text{ mA}/\mu s$	-	50	$A/\mu s$
$I_{GM}$	peak gate current		-	1	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	+150	$^{\circ}C$
$T_j$	junction temperature		-	125	$^{\circ}C$

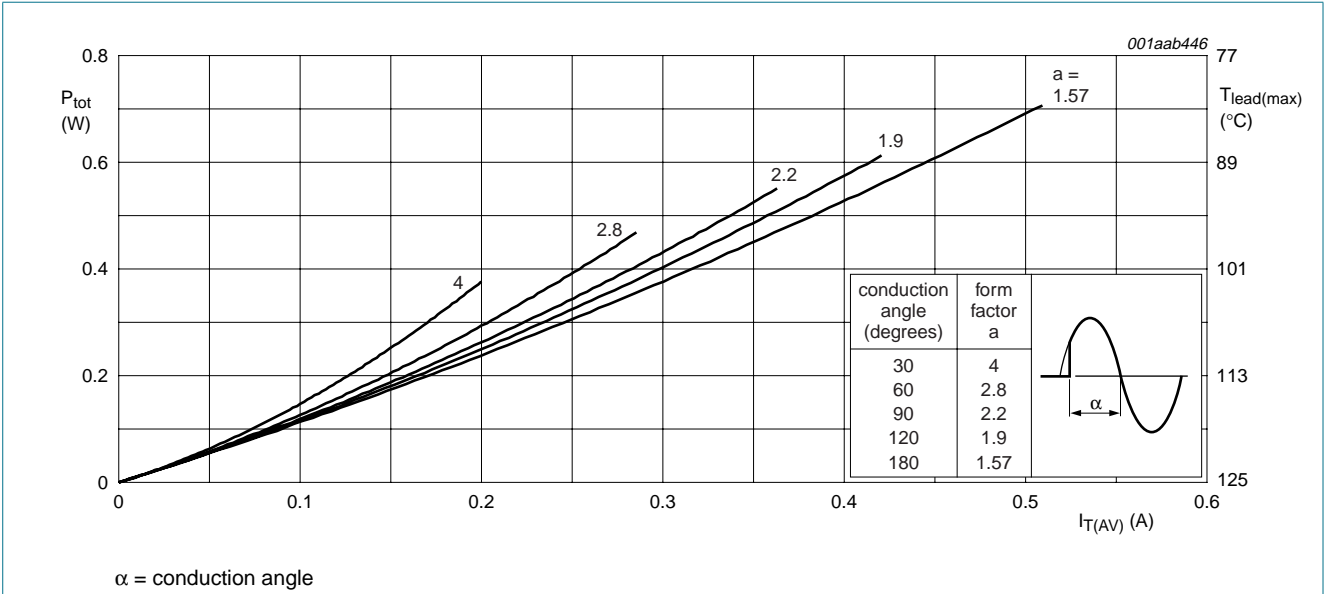


Fig 1. Total power dissipation as a function of average on-state current; maximum values

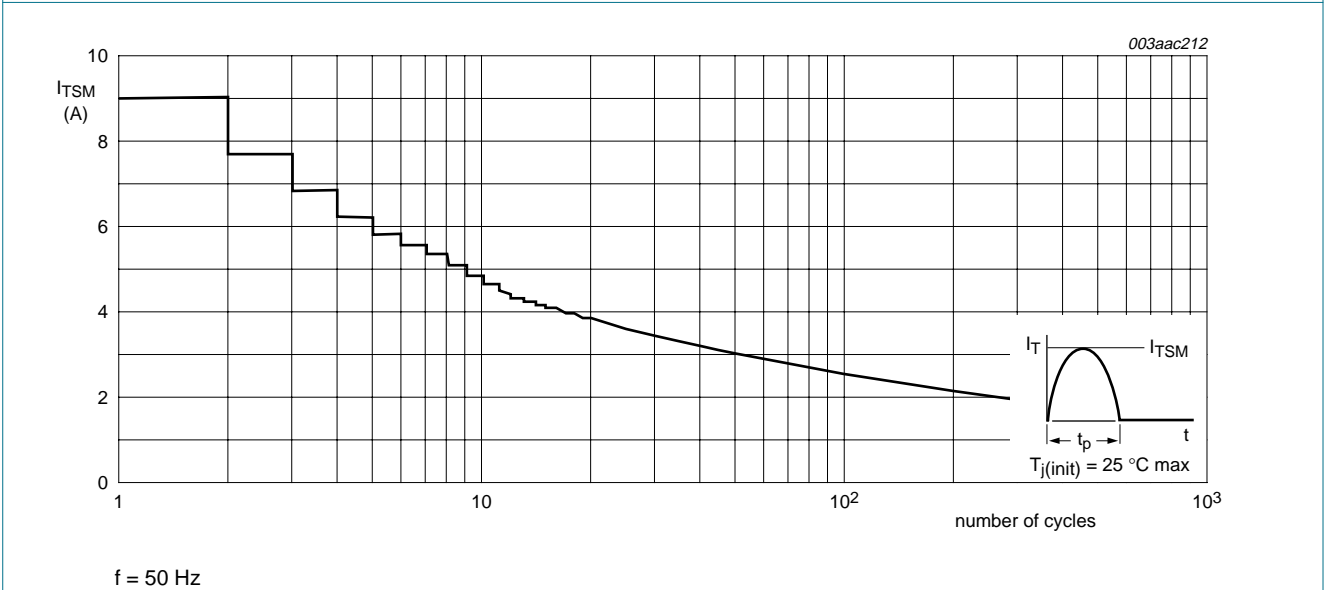
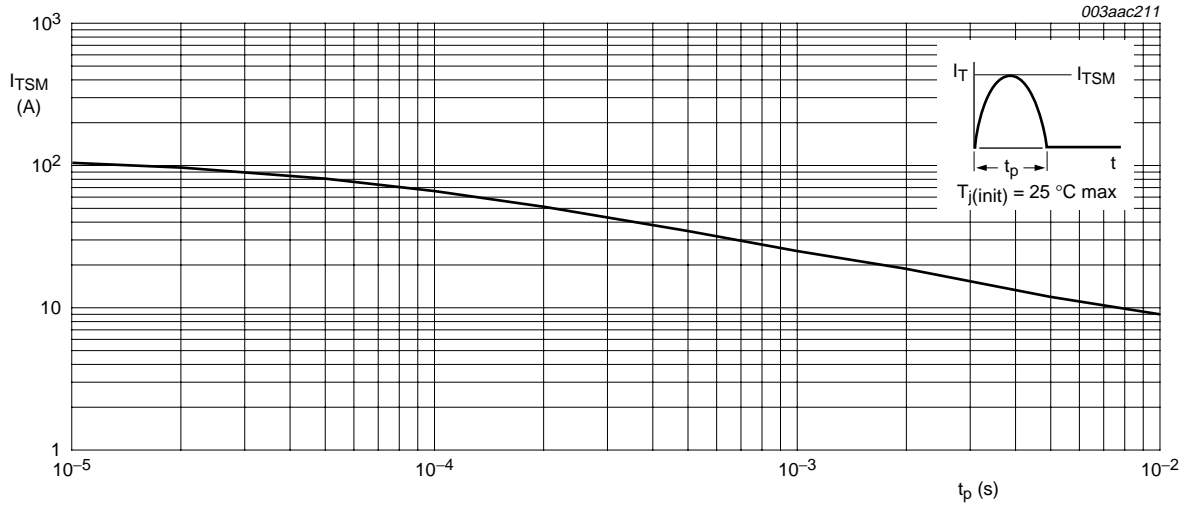
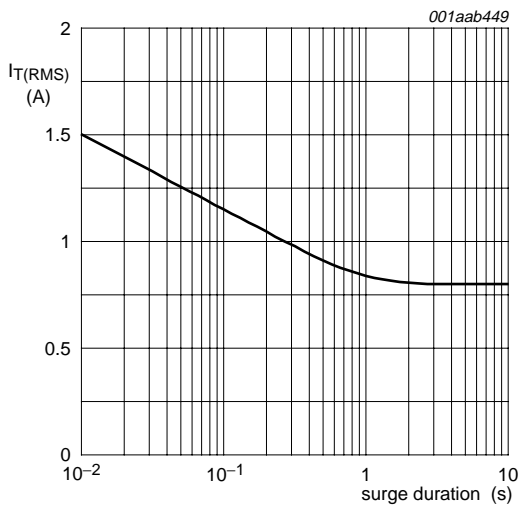


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



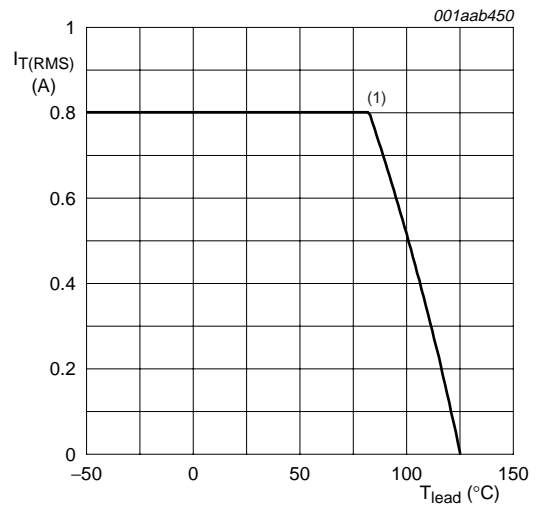
$t_p \leq 10 \text{ ms}$

**Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values**



$f = 50 \text{ Hz}$   
 $T_{\text{lead}} = 83 \text{ }^\circ\text{C}$

**Fig 4. RMS on-state current as a function of surge duration; maximum values**



(1)  $T_{\text{lead}} = 83 \text{ }^\circ\text{C}$

**Fig 5. RMS on-state current as a function of lead temperature; maximum values**

### 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	see <a href="#">Figure 6</a>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

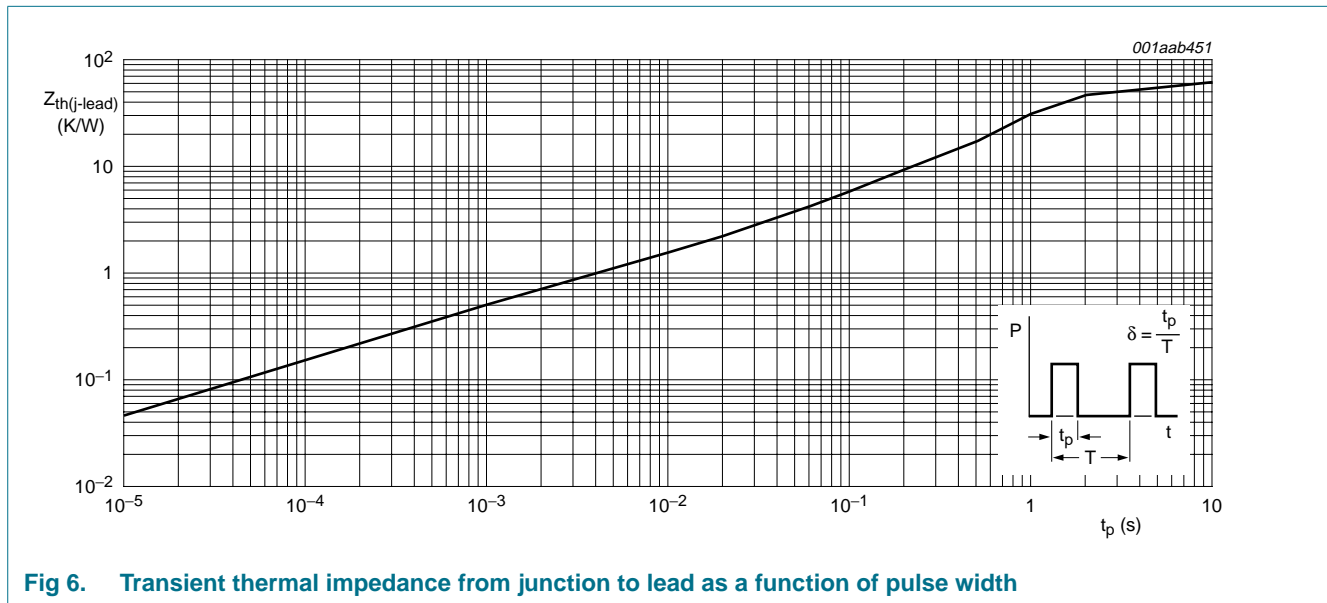


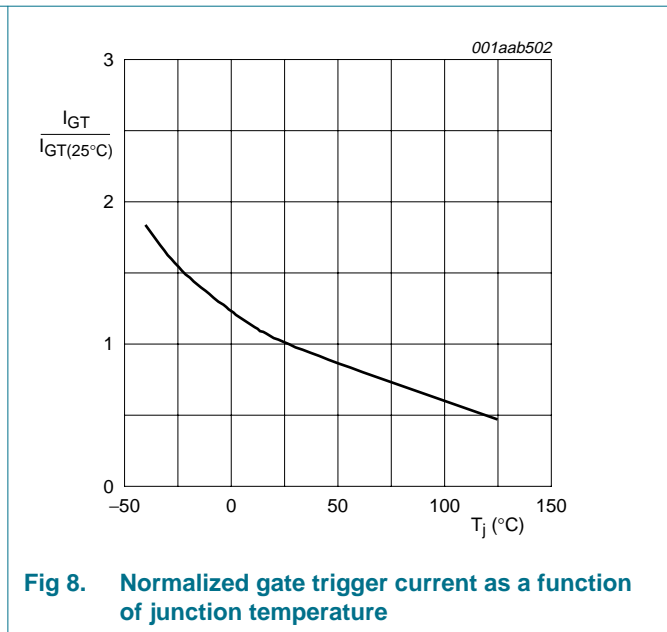
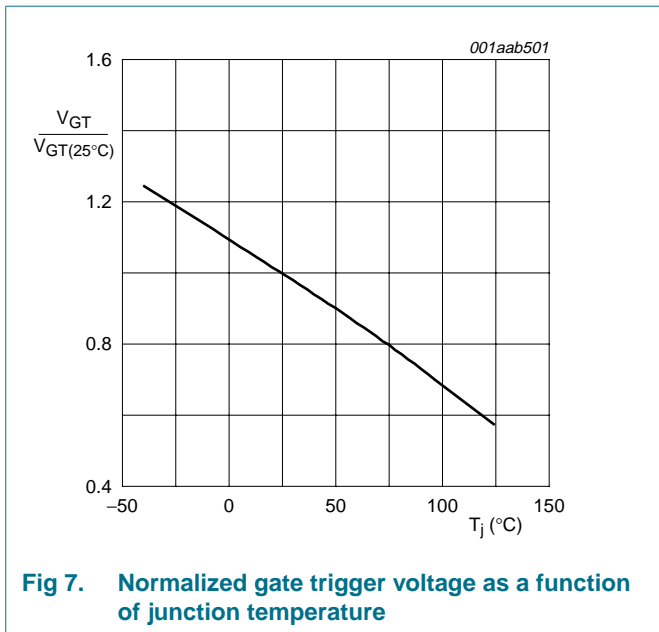
Fig 6. Transient thermal impedance from junction to lead as a function of pulse width

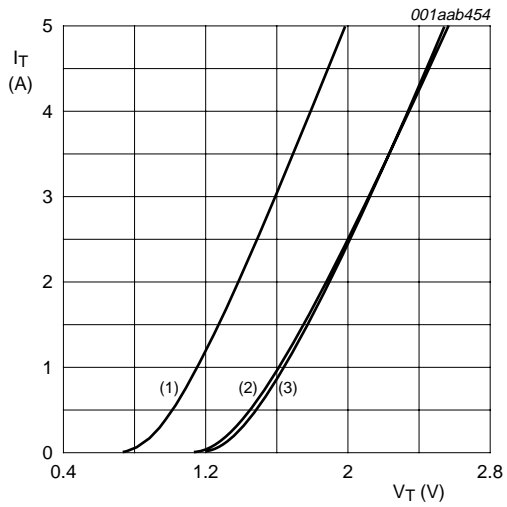
## 6. Characteristics

**Table 5. Characteristics**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

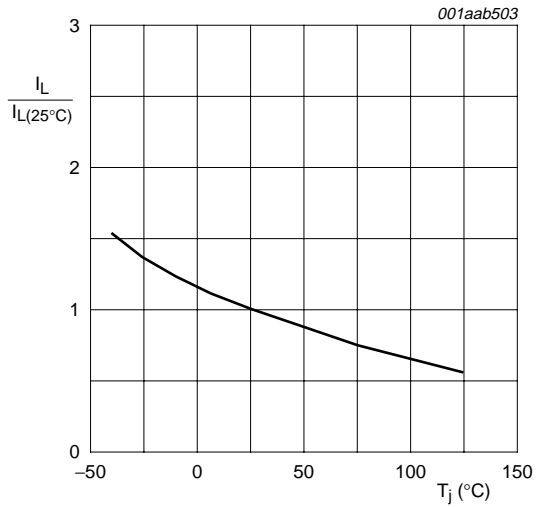
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; see <a href="#">Figure 8</a>	1	50	100	$\mu\text{A}$
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.5\text{ mA}$ ; $R_{GK} = 1\text{ k}\Omega$ ; see <a href="#">Figure 10</a>	-	2	6	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $I_G = 0.5\text{ mA}$ ; $R_{GK} = 1\text{ k}\Omega$ ; see <a href="#">Figure 11</a>	-	1.5	3	mA
$V_T$	on-state voltage	$I_T = 1.2\text{ A}$ ; see <a href="#">Figure 9</a>	-	1.25	1.7	V
$V_{GT}$	gate trigger voltage	$I_T = 10\text{ mA}$ ; see <a href="#">Figure 7</a>				
		$V_D = 12\text{ V}$	-	0.5	0.8	V
		$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$	0.2	0.3	-	V
$I_D$	off-state current	$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
$I_R$	reverse current	$V_R = V_{RRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; exponential waveform; see <a href="#">Figure 12</a>				
		$R_{GK} = 1\text{ k}\Omega$	150	350	-	$\text{V}/\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 2\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 10\text{ mA}$ ; $dI_G/dt = 0.1\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$
$t_q$	commutated turn-off time	$V_D = 0.67 \times V_{DRM(max)}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{TM} = 1.6\text{ A}$ ; $V_R = 35\text{ V}$ ; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$ ; $dV_D/dt = 2\text{ V}/\mu\text{s}$ ; $R_{GK} = 1\text{ k}\Omega$	-	100	-	$\mu\text{s}$





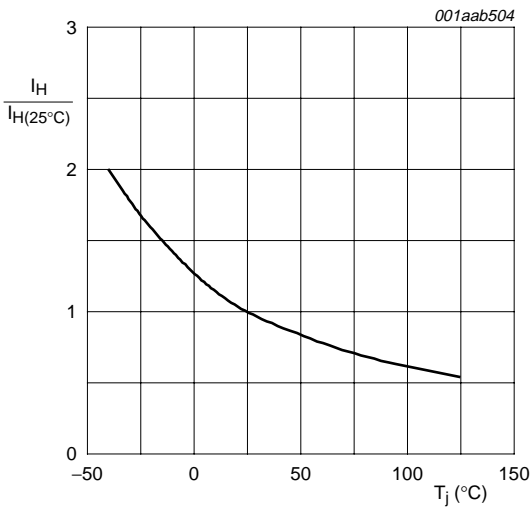
$V_o = 1.067\text{ V}$   
 $R_s = 0.187\ \Omega$   
 (1)  $T_j = 125\text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125\text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values

**Fig 9. On-state current as a function of on-state voltage**



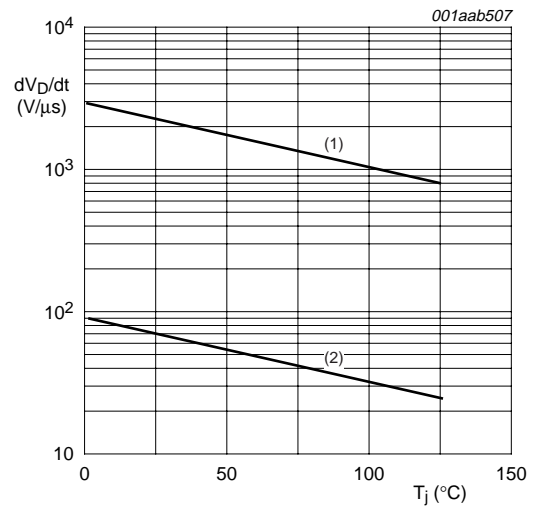
$R_{GK} = 1\text{ k}\Omega$

**Fig 10. Normalized latching current as a function of junction temperature**



$R_{GK} = 1\text{ k}\Omega$

**Fig 11. Normalized holding current as a function of junction temperature**



(1)  $R_{GK} = 1\text{ k}\Omega$   
 (2) Gate open circuit

**Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values**

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

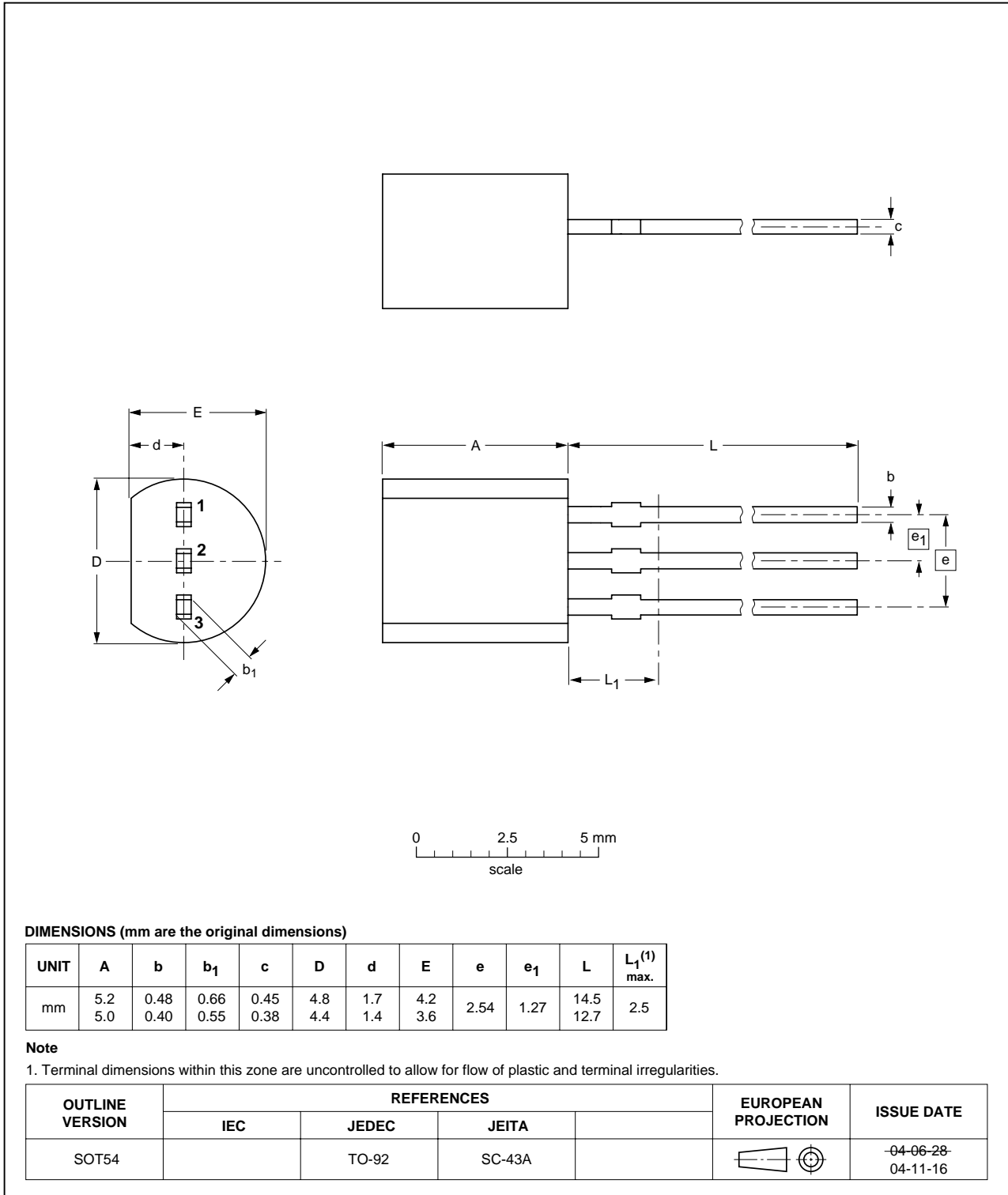


Fig 13. Package outline SOT54 (TO-92)



## 8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT169H_1	20080331	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 11. Contents

<b>1</b>	<b>Product profile</b> .....	<b>1</b>
1.1	General description .....	1
1.2	Features .....	1
1.3	Applications .....	1
1.4	Quick reference data .....	1
<b>2</b>	<b>Pinning information</b> .....	<b>1</b>
<b>3</b>	<b>Ordering information</b> .....	<b>2</b>
<b>4</b>	<b>Limiting values</b> .....	<b>2</b>
<b>5</b>	<b>Thermal characteristics</b> .....	<b>5</b>
<b>6</b>	<b>Characteristics</b> .....	<b>6</b>
<b>7</b>	<b>Package outline</b> .....	<b>8</b>
<b>8</b>	<b>Revision history</b> .....	<b>9</b>
<b>9</b>	<b>Legal information</b> .....	<b>10</b>
9.1	Data sheet status .....	10
9.2	Definitions .....	10
9.3	Disclaimers .....	10
9.4	Trademarks .....	10
<b>10</b>	<b>Contact information</b> .....	<b>10</b>
<b>11</b>	<b>Contents</b> .....	<b>11</b>

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